

SECTION II—CLAIMS

1. (Currently Amended) A method comprising:

determining a location of one or more regions on a reticle that come in contact with a reticle handling or support surface; and

generating a pattern to be written on the reticle, the pattern including one or more cut-out regions corresponding to the one or more regions that have been determined to come in contact with the reticle handling or support surface[[.]] :

and

adjusting the position, size or shape of one or more of the cut-out regions in the pattern to avoid conflict between the one or more cut-out regions and a required feature of the reticle.

2. (Original) The method of claim 1, wherein determining a location of the one or more regions comprises determining a type of support surface used for the reticle.
3. (Original) The method of claim 1, wherein determining a location of the one or more regions comprises determining a type of carrier used for the reticle.
4. (Original) The method of claim 1, wherein determining a location of the one or more regions comprises determining a type of handling apparatus used for the reticle.
5. (Original) The method of claim 1, wherein determining a location of the one or more regions comprises determining a type of storage apparatus used for the reticle.

6. (Original) The method of claim 1, wherein determining a location of the one or more regions comprises determining a manufacturing process used with the reticle.
7. (Original) The method of claim 6, wherein determining a location of the one or more regions comprises determining one or more required features to be written on the reticle.
8. (Original) The method of claim 1, further comprising determining a size of each cut-out region.
9. (Original) The method of claim 1, further comprising writing the pattern on a reticle blank.
10. (Original) The method of claim 9, further comprising developing and etching the pattern to remove reticle surface chrome from the regions that have been determined to come in contact with the reticle handling or support surface.
11. (Currently Amended) A reticle comprising:
 - a circuit pattern to be exposed on a wafer; and
 - one or more chrome cut-out regions positioned where a reticle handling or support apparatus has been determined to come in contact with the reticle[.].
wherein the position, size or shape of one or more of the cut-out regions can be adjusted to avoid conflict between the one or more cut-out regions and a required feature of the reticle.
12. (Original) The reticle of claim 11, further comprising a barcode.
13. (Original) The reticle of claim 11, further comprising an alignment feature.

14. (Original) The reticle of claim 11, further comprising a pellicle to shield the reticle from particles.

15. (Original) The reticle of claim 11, further comprising a reticle manufacturing structure.

16. (Currently Amended) A method comprising:

writing a pattern on a blank reticle having a layer of photoresist and a layer of chrome, the pattern including one or more cut-out regions that have been determined to come in contact with a reticle handling or support apparatus, wherein the position, size or shape of one or more of the cut-out regions in the pattern can be adjusted to avoid conflict between the one or more cut-out regions and a required feature of the reticle;

developing the pattern to remove the photoresist layer and reveal the chrome layer in the regions determined to come in contact with the reticle handling or support apparatus; and

etching away the chrome layer to remove chrome from the regions determined to come in contact with the reticle handling or support apparatus.

17. (Original) The method of claim 16, wherein the layer of photoresist is positive and developing the pattern comprises exposing and removing the photoresist layer from the written regions to reveal the chrome layer.

18. (Original) The method of claim 17, wherein etching away the chrome layer comprises etching away the chrome layer from the written regions to reveal a glass layer of the reticle.

19. (Original) The method of claim 16, wherein the layer of photoresist is negative and developing the pattern comprises exposing and removing the photoresist layer from the unwritten regions to reveal the chrome layer.
20. (Original) The method of claim 19, wherein etching away the chrome layer comprises etching away the chrome layer from the unwritten regions to reveal a glass layer of the reticle.
21. (Original) The method of claim 16, wherein writing a pattern on a blank reticle comprises writing a pattern on a blank reticle via an E-beam machine.
22. (Original) The method of claim 16, wherein writing a pattern on a blank reticle comprises writing a pattern on a blank reticle via a laser writer.
23. (New) A method comprising:
 - writing a pattern on a blank reticle having a layer of photoresist and a layer of chrome, the pattern including one or more cut-out regions that have been determined to come in contact with a reticle handling or support apparatus;
 - developing the pattern to remove the photoresist layer and reveal the chrome layer in the regions determined to come in contact with the reticle handling or support apparatus, wherein the layer of photoresist is positive and developing the pattern comprises exposing and removing the photoresist layer from the written regions to reveal the chrome layer; and
 - etching away the chrome layer to remove chrome from the regions determined to come in contact with the reticle handling or support apparatus.

24. (New) The method of claim 23, wherein etching away the chrome layer comprises etching away the chrome layer from the written regions to reveal a glass layer of the reticle.

25. (New) A method comprising:

writing a pattern on a blank reticle having a layer of photoresist and a layer of chrome, the pattern including one or more cut-out regions that have been determined to come in contact with a reticle handling or support apparatus;

developing the pattern to remove the photoresist layer and reveal the chrome layer in the regions determined to come in contact with the reticle handling or support apparatus, wherein the layer of photoresist is negative and developing the pattern comprises exposing and removing the photoresist layer from the unwritten regions to reveal the chrome layer; and

etching away the chrome layer to remove chrome from the regions determined to come in contact with the reticle handling or support apparatus.

26. (New) The method of claim 25, wherein etching away the chrome layer comprises etching away the chrome layer from the unwritten regions to reveal a glass layer of the reticle.